



Super Fast Reconery Rectifiers Diodes ES1A ES1B ES1C ES1D ES1F ES1G ES1H ES1J

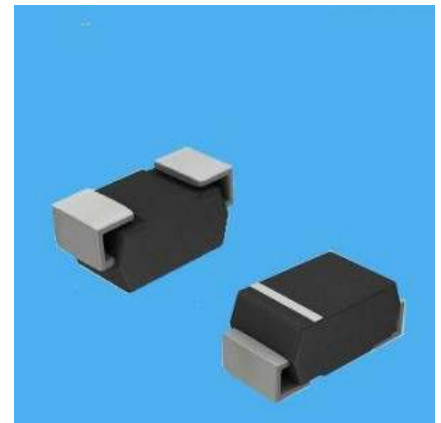
Specifications

1A Super Fast Reconery Rectifiers Diodes ES1A ES1B ES1C ES1D ES1F ES1G ES1H ES1J IN SMA PACKAGE

- 1)IF(A):1.0A
- 2) VRRM (V): 50V
- 3)IFSM (A):30A
- 4) VF (V): 0.95V
- 5)IR (μA)TA=25oC:5μA
- 6) Case Style:SMA/DO-214AC

Features:

- 1)For surface mounted application
- 2)Low profile package
- 3)Low power loss,high efficiency
- 4)Ideal for automated placement
- 5)Glass passivated chip junction
- 6)High temperature soldering: 260°c /10 seconds at terminals



Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%

Type Number	Symbol	ES 1A	ES 1B	ES 1C	ES 1D	ES 1F	ES 1G	ES 1H	ES 1J	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	150	200	300	400	500	600	V
Maximum RMS Voltage	V _{RMS}	35	70	105	140	210	280	350	420	V
Maximum DC Blocking Voltage	V _{DC}	50	100	150	200	300	400	500	600	V
Maximum Average Forward Rectified Current See Fig. 1	I _(AV)	1.0								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	30								A
Maximum Instantaneous Forward Voltage @ 1.0A	V _F	0.95			1.3		1.7			V
Maximum DC Reverse Current @ T _A =25 °C at Rated DC Blocking Voltage @ T _A =100 °C	I _R					5.0				uA
						100				uA
Maximum Reverse Recovery Time (Note 1)	T _{rr}					35				nS
Typical Junction Capacitance (Note 2)	C _j	10			8					pF
Maximum Thermal Resistance (Note 3)	R _{θJA} R _{θJL}					85				°C /W
						35				
Operating Temperature Range	T _j					-55 to +150				°C
Storage Temperature Range	T _{STG}					-55 to +150				°C

- Notes:
- 1. Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A
 - 2. Measured at 1 MHz and Applied VR=4.0 Volts
 - 3. P.C.B. Mounted on 0.2 x 0.2" (5.0 x 5.0mm) Copper Pad Area.